

Features

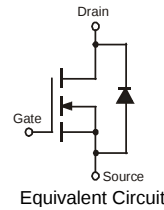
- Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- High Drain-Source Voltage Rating
- **Lead, Halogen and Antimony Free, RoHS Compliant "Green" Device (Notes 2 and 4)**

Mechanical Data

- Case: SOT-23
- Case Material: Molded Plastic. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020C
- Terminals: Solderable per MIL-STD-202, Method 208
- Lead Free Plating (Matte Tin Finish annealed over Alloy 42 leadframe).
- Terminal Connections: See Diagram
- Marking Information: See Page 3
- Ordering Information: See Page 3
- Weight: 0.008 grams (approximate)

BSS123

N-Channel MOSFET



1.Gate
2.Source
3.Drain

SOT-23

Maximum Ratings @T_A = 25°C unless otherwise specified

Characteristic	Symbol	Value	Units
Drain-Source Voltage	V _{DSS}	100	V
Drain-Gate Voltage R _{GS} ≤ 20KΩ	V _{DGR}	100	V
Gate-Source Voltage Continuous	V _{GSS}	±20	V
Drain Current (Note 1) Continuous	I _D	170	mA
Pulsed	I _{DM}	680	

Thermal Characteristics @T_A = 25°C unless otherwise specified

Characteristic	Symbol	Value	Units
Total Power Dissipation (Note 1)	P _d	300	mW
Thermal Resistance, Junction to Ambient (Note 1)	R _{θJA}	417	°C/W
Operating and Storage Temperature Range	T _j , T _{STG}	-55 to +150	°C

Electrical Characteristics @T_A = 25°C unless otherwise specified

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 3)						
Drain-Source Breakdown Voltage	BV _{DSS}	100	—	—	V	V _{GS} = 0V, I _D = 250μA
Zero Gate Voltage Drain Current	I _{DSS}	—	—	1.0 10	μA nA	V _{DS} = 100V, V _{GS} = 0V V _{DS} = 20V, V _{GS} = 0V
Gate-Body Leakage, Forward	I _{GSSF}	—	—	50	nA	V _{GS} = 20V, V _{DS} = 0V
ON CHARACTERISTICS (Note 3)						
Gate Threshold Voltage	V _{GS(th)}	0.8	1.4	2.0	V	V _{DS} = V _{GS} , I _D = 1mA
Static Drain-Source On-Resistance	R _{DS (ON)}	— —	— —	6.0 10	Ω	V _{GS} = 10V, I _D = 0.17A V _{GS} = 4.5V, I _D = 0.17A
Forward Transconductance	g _{FS}	80	370	—	mS	V _{DS} = 10V, I _D = 0.17A, f = 1.0KHz
Drain-Source Diode Forward Voltage	V _{SD}	—	0.84	1.3	V	V _{GS} = 0V, I _S = 0.34A
DYNAMIC CHARACTERISTICS						
Input Capacitance	C _{iss}	—	29	60	pF	V _{DS} = 25V, V _{GS} = 0V, f = 1.0MHz
Output Capacitance	C _{oss}	—	10	15	pF	
Reverse Transfer Capacitance	C _{rss}	—	2	6	pF	
SWITCHING CHARACTERISTICS						
Turn-On Rise Time	t _r	—	—	8	ns	V _{DD} = 30V, I _D = 0.28A, R _{GEN} = 50Ω, V _{GS} = 10V
Turn-Off Fall Time	t _f	—	—	16	ns	
Turn-On Delay Time	t _{D(ON)}	—	—	8	ns	
Turn-Off Delay Time	t _{D(OFF)}	—	—	13	ns	

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